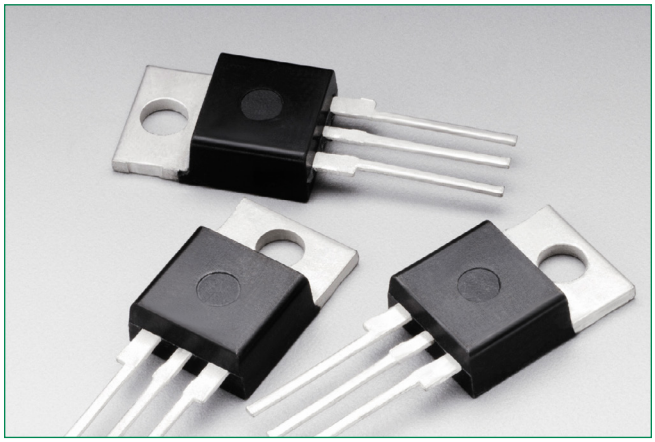
MCR8SDG, MCR8SMG, MCR8SNG

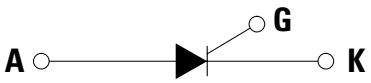
Sensitive Gate Silicon Controlled Rectifiers — 400V - 800V



Additional Information

Resources | Accessories | Samples

Functional Diagram



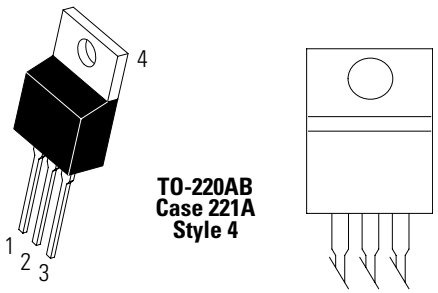
Description

Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half−wave, silicon gate−controlled devices are needed.

Features

- Sensitive Gate Allows Triggering by Microcontrollers and other Logic Circuits
- Blocking Voltage to 800 V
- On−State Current Rating of 8 A RMS at 80°C
- High Surge Current Capability − 80 A
- Rugged, Economical TO−220AB Package
- Glass Passivated Junctions for Reliability and Uniformity
- Minimum and Maximum Values of IGT, VGT and IH Specified for Ease of Design
- Immunity to dv/dt − 5 V/μsec Minimum at 110°C
- These are Pb−Free Devices

Pin Out



TO-220AB
Case 221A
Style 4

Revised: GD. 05/24/21

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Maximum Ratings (T_J = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off–State Voltage (Note 1) (– 40 to 110°C, Sine Wave, 50 to 60 Hz, Gate Open)	MCR8SDG MCR8SMG MCR8SNG	V_{DRM}, V_{RRM}	400 600 800	V
On-State RMS Current (180° Conduction Angles; T_C = 80°C)		$I_{T\ (RMS)}$	8.0	A
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave 60 Hz, T_J = 110°C)		I_{TSM}	80	A
Circuit Fusing Consideration (t = 8.33 ms)		I^2t	26.5	A^2sec
Forward Peak Gate Power (Pulse Width ≤ 10 µsec, T_C = 80°C)		P_{GM}	5.0	W
Forward Average Gate Power (t = 8.3 msec, T_C = 80°C)		$P_{GM\ (AV)}$	0.5	W
Forward Peak Gate Current (Pulse Width ≤ 10 µsec, T_C= 80°C)		I_{GM}	2.0	A
Operating Junction Temperature Range		T_J	-40 to 110	°C
Storage Temperature Range		T_{stg}	-40 to 150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

Thermal Characteristics

Rating	Symbol	Value	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Junction–to–Ambient	$R_{\theta JA}$	62.5	
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	°C

Electrical Characteristics - OFF (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Repetitive Forward or Reverse Blocking Current (Note 3) (V_{AK} = Rated V_{DRM} or V_{RRM}, R_{GK} = 1.0 kΩ	T_J = 25°C	I_{DRM}, I_{RRM}	-	-	10	µA
	T_J = 110°C		-	-	500	

Electrical Characteristics - ON (T_J = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Typ	Max	Unit
Peak Forward On–State Voltage (Note 2) (I_{TM} = 16 A)		V_{TM}	-	-	1.8	V
Gate Trigger Current (Continuous dc) (Note 4) (V_D = 12 V; R_L = 100 Ω)		I_{GT}	5.0	25	200	µA
Holding Current (Note 3) (V_D = 12 V, Gate Open, Initiating Current = 200 mA)		I_H	-	0.5	6.0	mA
Latch Current (Note 4) (V_D = 12 V, I_G = 200 µA)		I_L	-	0.6	8.0	mA
Gate Trigger Voltage (Continuous dc) (V_D = 12 V, R_L = 100 Ω) (Note 4)	T_J = 25°C	V_{GT}	0.3	0.65	1.0	V
	T_J = –40°C		-	-	1.5	
Gate Non–Trigger Voltage (V_D = 12 V, R_L = 100 Ω)	T_J = 110°C	V_{GD}	0.2	-	-	V

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Dynamic Characteristics

Characteristic	Symbol	Min	Typ	Max	Unit
Critical Rate of Rise of Off−State Voltage (V_D = 67% V_{DRM}, R_{GK} = 1 KΩ, C_{GK} = 0.1 μF, T_J = 110ºC)	dv/dt	5.0	15	–	V/μs
Critical Rate of Rise of On−State Current (IPK = 50 A, Pw = 40 μsec, diG/dt = 1 A/μsec, Igt = 10 mA	di/dt	–	–	100	A/μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Ratings apply for negative gate voltage or RGK = 1.0 kΩ. Devices shall not have a positive gate voltage concurrently with a negative voltage on the anode. Devices should not be tested with a constant current source for forward and reverse blocking capability such that the voltage applied exceeds the rated blocking voltage.
3. Pulse Test; Pulse Width ≤ 2.0 msec, Duty Cycle ≤ 2%.
4. RGK current not included in measurements.

Voltage Current Characteristic of SCR

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current

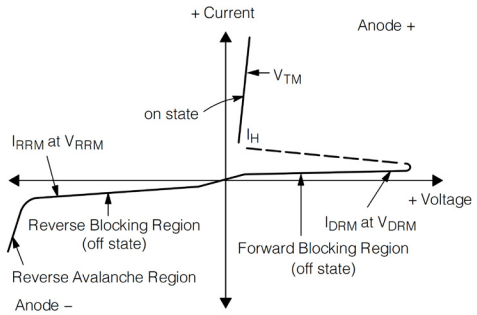

Figure 1.
Typical RMS Current Derating

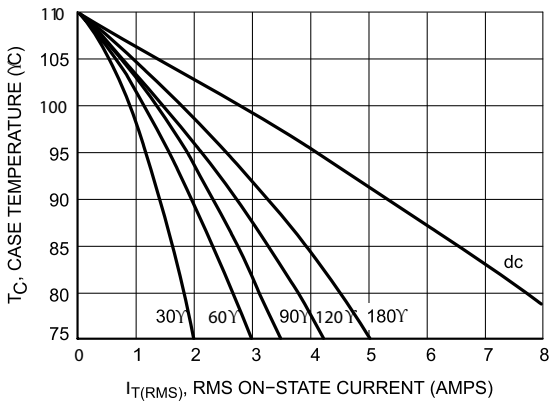

Figure 2.
On−State Power Dissipation

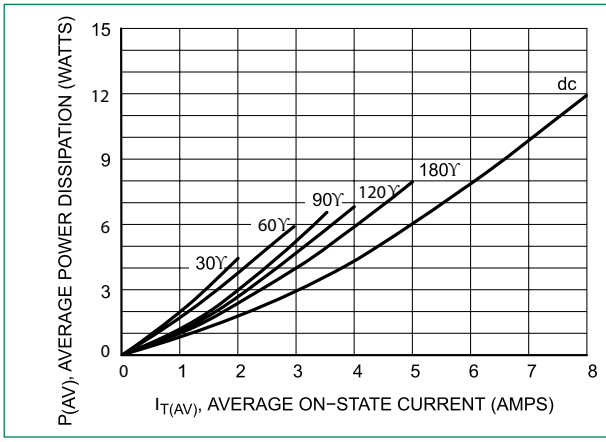

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Figure 3.
Typical On–State Characteristics

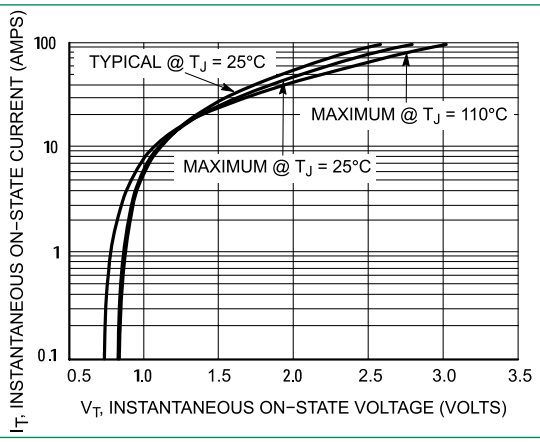


Figure 4.
Typical Gate Trigger Current vs Junction Temperature

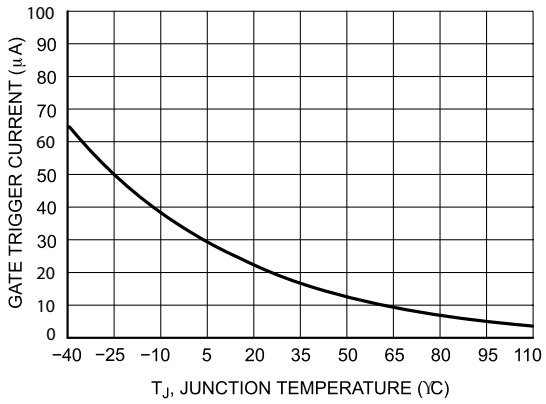


Figure 5.
Typical Gate Trigger Current vs Junction Temperature

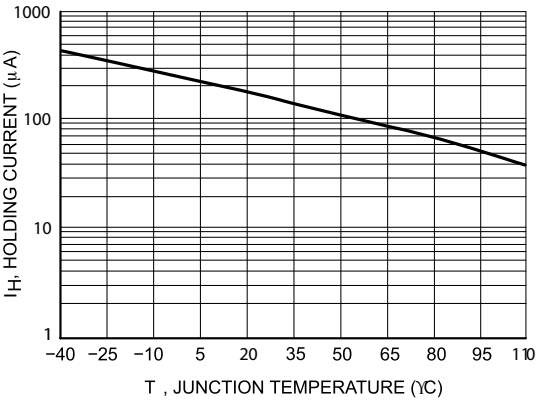


Figure 6.
Typical Gate Trigger Voltage vs Junction Temperature

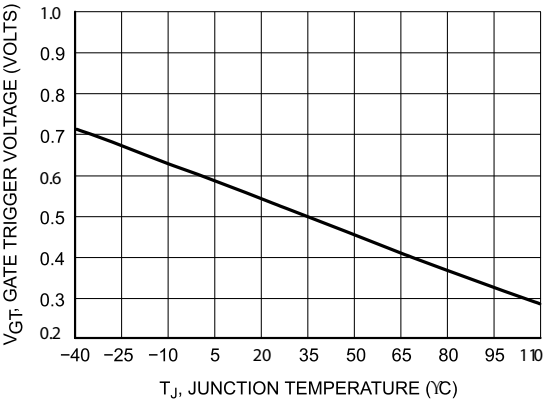
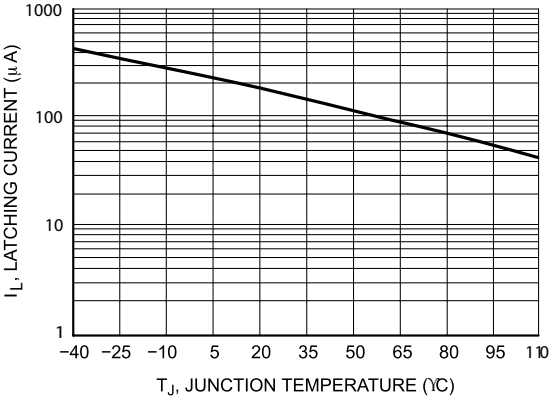


Figure 7.
Typical Holding Current vs Junction Temperature



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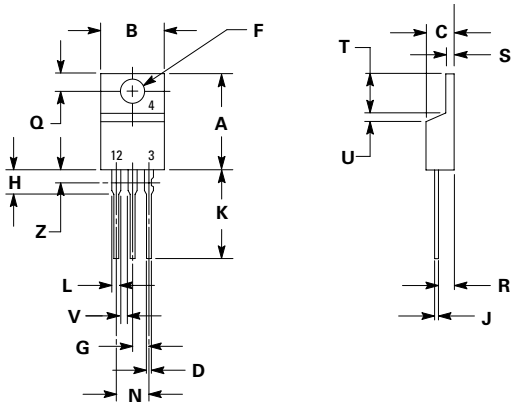
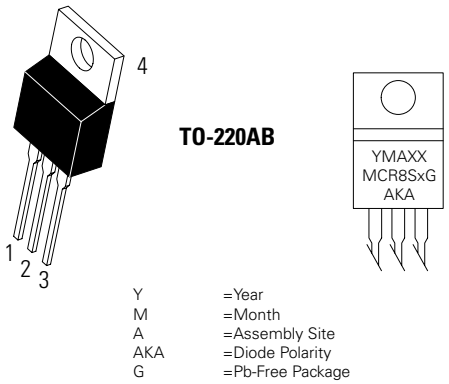
Dimensions



Part Marking System



Y	=Year
M	=Month
A	=Assembly Site
AKA	=Diode Polarity
G	=Pb-Free Package

Dim	Inches		Millimeters	
	Min	Max	Min	Max
A	0.590	0.620	14.99	15.75
B	0.380	0.420	9.65	10.67
C	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
F	0.142	0.147	3.61	3.73
G	0.095	0.105	2.41	2.67
H	0.110	0.130	2.79	3.30
J	0.018	0.024	0.46	0.61
K	0.540	0.575	13.72	14.61
L	0.060	0.075	1.52	1.91
N	0.195	0.205	4.95	5.21
Q	0.105	0.115	2.67	2.92
R	0.085	0.095	2.16	2.41
S	0.045	0.060	1.14	1.52
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

1. Dimensioning and tolerancing per ansi y14.5m, 1982.
2. Controlling dimension: inch.
3. Dimension z defines a zone where all body and lead irregularities are allowed.

Pin Assignment	
1	Cathode
2	Anode
3	Gate
4	Anode

Ordering Information

Device	Package	Shipping
MCR8SDG	TO–220AB (Pb–Free)	1000 Units / Box
MCR8SMG		
MCR8SNG		